



PMEG2020CPAS

20 V, 2 A low VF dual MEGA Schottky barrier rectifier

20 January 2015

Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier in common cathode configuration with an integrated guard ring for stress protection, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current $I_{F(AV)} \leq 2$ A
- Reverse voltage $V_R \leq 20$ V
- Low forward voltage $V_F \leq 420$ mV
- Low reverse current
- Reduced Printed-Circuit-Board (PCB) area requirements
- Exposed heat sink (cathode pad) for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with visible and solderable side pads
- Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Free-wheeling application
- Reverse polarity protection
- Low power consumption application
- Battery chargers for mobile equipment
- LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per diode							
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20$ kHz; $T_{amb} \leq 80$ °C; square wave	[1]	-	-	2	A
		$\delta = 0.5$; $f = 20$ kHz; $T_{sp} \leq 140$ °C; square wave		-	-	2	A

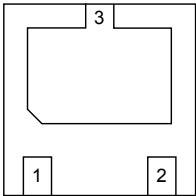
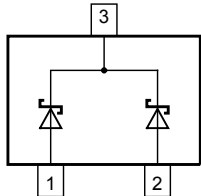


Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_R	reverse voltage	$T_j = 25\text{ }^{\circ}\text{C}$	-	-	20	V
Per diode						
V_F	forward voltage	$I_F = 2\text{ A}$; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_j = 25\text{ }^{\circ}\text{C}$; pulsed	-	385	420	mV
I_R	reverse current	$V_R = 20\text{ V}$; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_j = 25\text{ }^{\circ}\text{C}$; pulsed	-	380	1000	μA

[1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	anode diode 1	A1	 Transparent top view DFN2020D-3 (SOT1061D)	 006aaa438
2	anode diode 2	A2		
3	common cathode	K		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG2020CPAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061D

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG2020CPAS	CW

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V_R	reverse voltage	$T_j = 25\text{ }^{\circ}\text{C}$		-	20	V
I_F	forward current	$T_{sp} \leq 135\text{ }^{\circ}\text{C}; \delta = 1$		-	2.8	A
$I_{F(AV)}$	average forward current	$\delta = 0.5; f = 20\text{ kHz}; T_{amb} \leq 80\text{ }^{\circ}\text{C};$ square wave	[1]	-	2	A
		$\delta = 0.5; f = 20\text{ kHz}; T_{sp} \leq 140\text{ }^{\circ}\text{C};$ square wave		-	2	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1\text{ ms}; \delta \leq 0.25$		-	7	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}; T_{j(init)} = 25\text{ }^{\circ}\text{C};$ square wave		-	9	A
Per device; one diode loaded						
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	[2]	-	500	mW
			[3]	-	960	mW
			[1]	-	1800	mW
T_j	junction temperature			-	150	$^{\circ}\text{C}$
T_{amb}	ambient temperature			-55	150	$^{\circ}\text{C}$
T_{stg}	storage temperature			-65	150	$^{\circ}\text{C}$

[1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per device; one diode loaded							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	250	K/W
			[1][3]	-	-	130	K/W
			[1][4]	-	-	70	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.

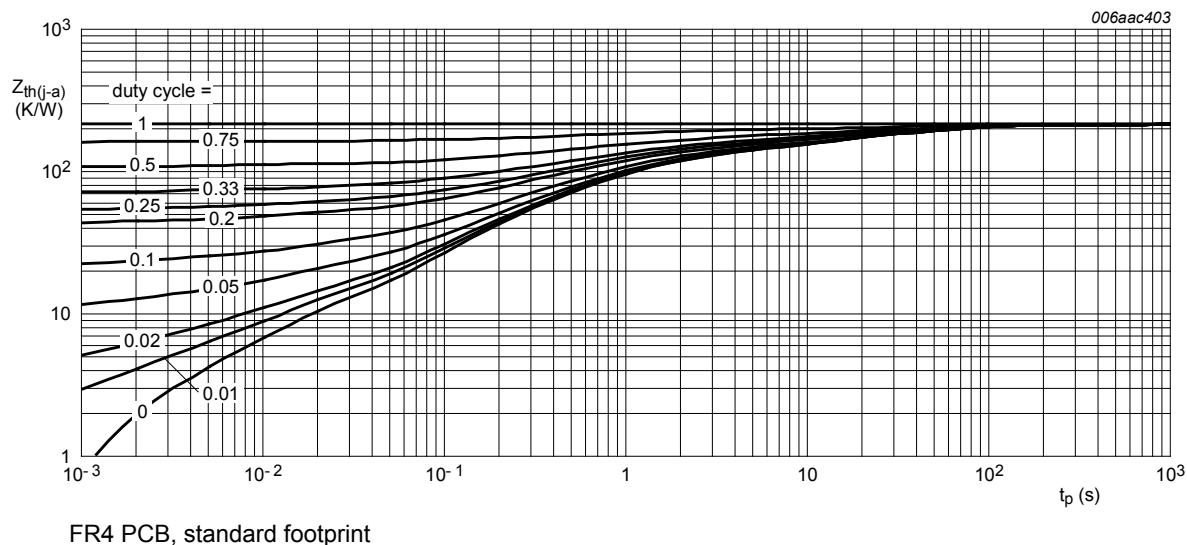
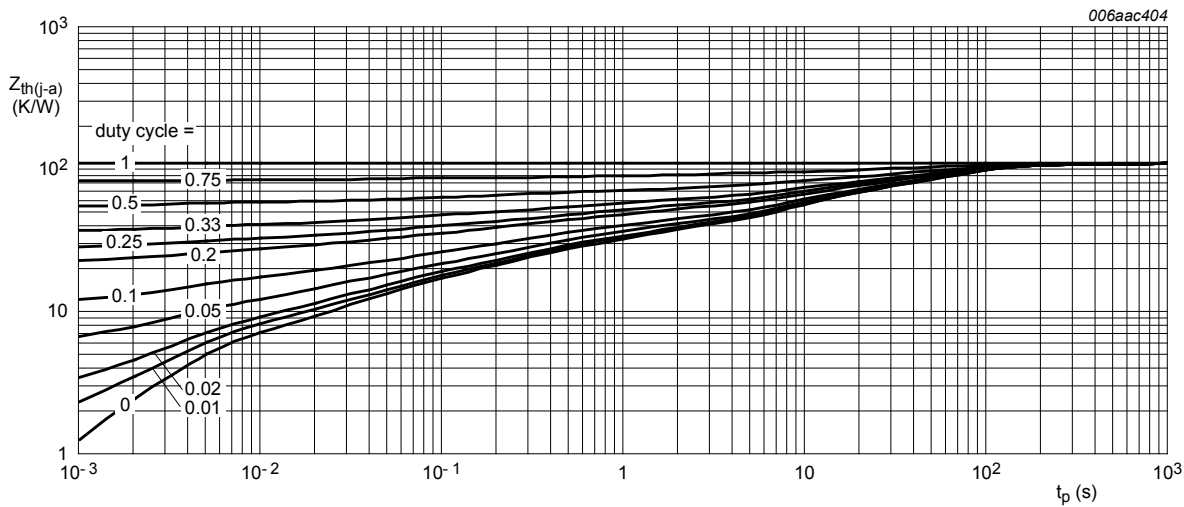
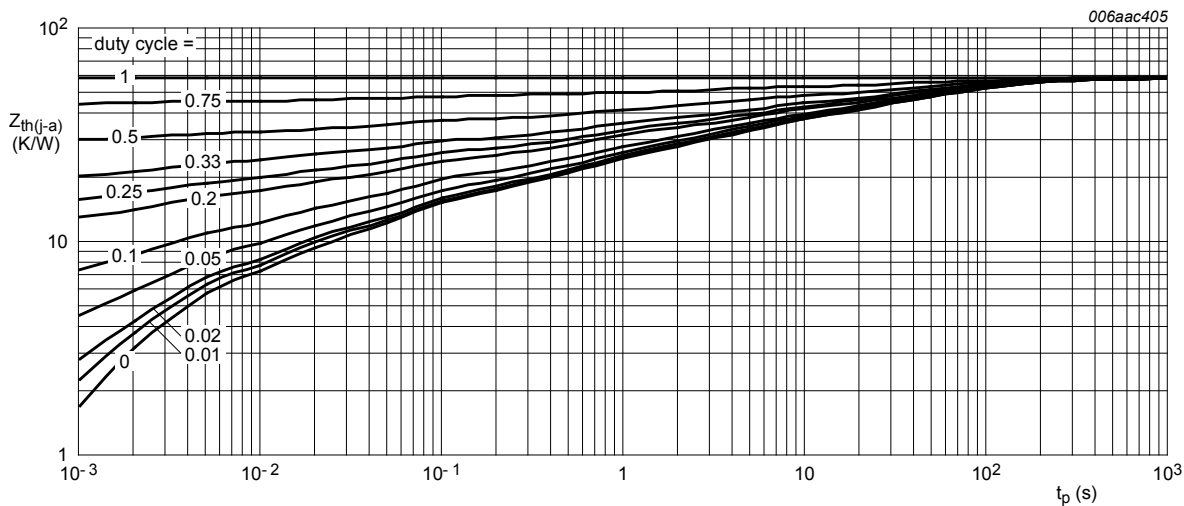


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm²

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



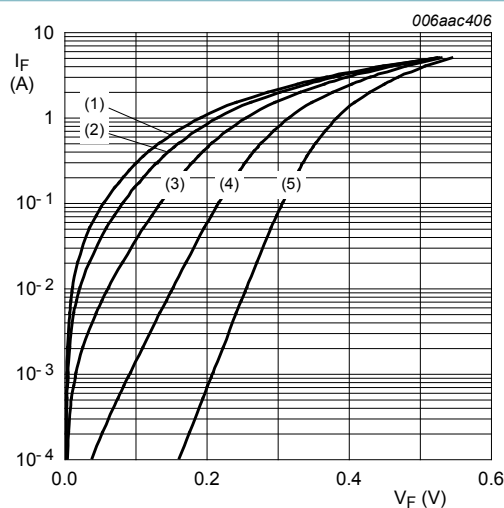
Ceramic PCB, Al₂O₃, standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

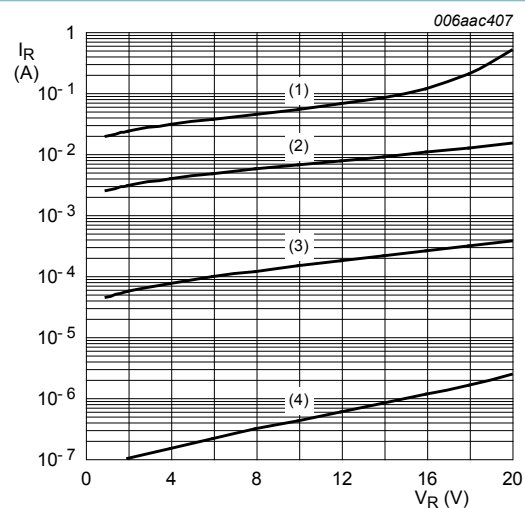
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per diode						
$V_{(BR)R}$	reverse breakdown voltage	$I_R = 5 \text{ mA}$; $T_J = 25 \text{ }^\circ\text{C}$; $t_p = 300 \text{ } \mu\text{s}$; $\delta = 0.02$; pulsed	20	-	-	V
V_F	forward voltage	$I_F = 100 \text{ mA}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ }^\circ\text{C}$; pulsed	-	220	-	mV
		$I_F = 1 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ }^\circ\text{C}$; pulsed	-	320	360	mV
		$I_F = 2 \text{ A}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ }^\circ\text{C}$; pulsed	-	385	420	mV
I_R	reverse current	$V_R = 10 \text{ V}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ }^\circ\text{C}$; pulsed	-	160	-	μA
		$V_R = 20 \text{ V}$; $t_p \leq 300 \text{ } \mu\text{s}$; $\delta \leq 0.02$; $T_J = 25 \text{ }^\circ\text{C}$; pulsed	-	380	1000	μA
C_d	diode capacitance	$V_R = 1 \text{ V}$; $f = 1 \text{ MHz}$; $T_J = 25 \text{ }^\circ\text{C}$	-	175	-	pF
		$V_R = 10 \text{ V}$; $f = 1 \text{ MHz}$; $T_J = 25 \text{ }^\circ\text{C}$	-	65	-	pF
t_{rr}	reverse recovery time	$I_F = 10 \text{ mA}$; $I_R = 10 \text{ mA}$; $R_L = 100 \text{ } \Omega$; $I_{R(\text{meas})} = 1 \text{ mA}$; $T_J = 25 \text{ }^\circ\text{C}$	-	55	-	ns



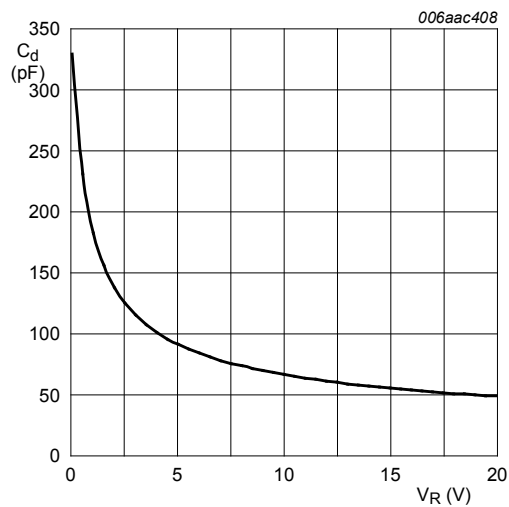
- (1) $T_J = 150 \text{ }^\circ\text{C}$
- (2) $T_J = 125 \text{ }^\circ\text{C}$
- (3) $T_J = 85 \text{ }^\circ\text{C}$
- (4) $T_J = 25 \text{ }^\circ\text{C}$
- (5) $T_J = -40 \text{ }^\circ\text{C}$

Fig. 4. Forward current as a function of forward voltage; typical values



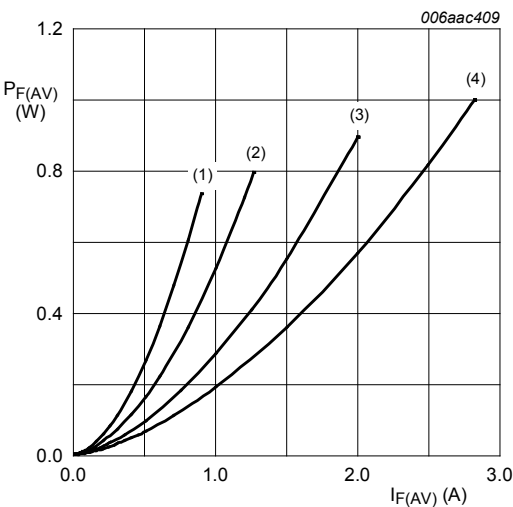
- (1) $T_J = 125 \text{ }^\circ\text{C}$
- (2) $T_J = 85 \text{ }^\circ\text{C}$
- (3) $T_J = 25 \text{ }^\circ\text{C}$
- (4) $T_J = -40 \text{ }^\circ\text{C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values



$f = 1\text{ MHz}; T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$

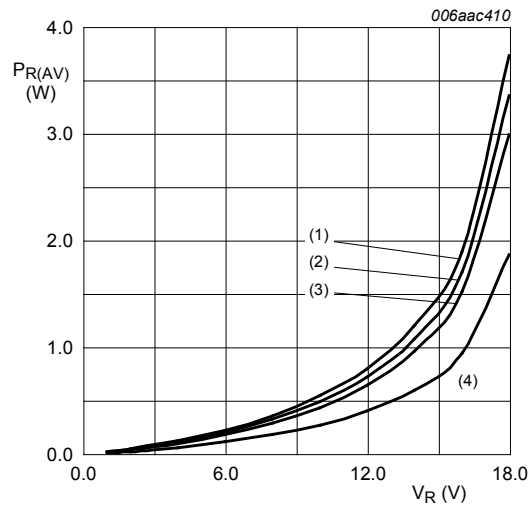
Fig. 6. Diode capacitance as a function of reverse voltage; typical values



$T_j = 150\text{ }^{\circ}\text{C}$

- (1) $\delta = 0.1$
- (2) $\delta = 0.2$
- (3) $\delta = 0.5$
- (4) $\delta = 1$

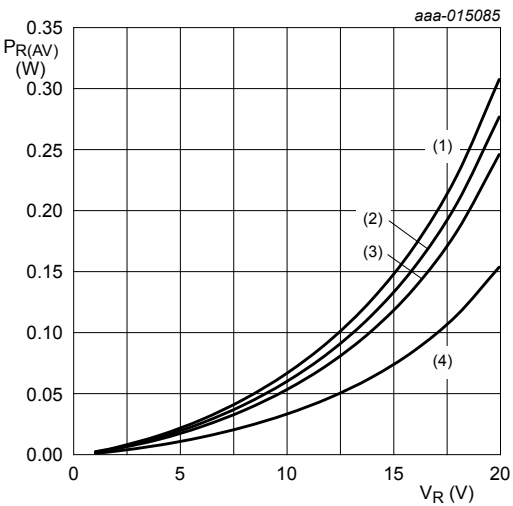
Fig. 7. Average forward power dissipation as a function of average forward current; typical values



$T_j = 125\text{ }^{\circ}\text{C}$

- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

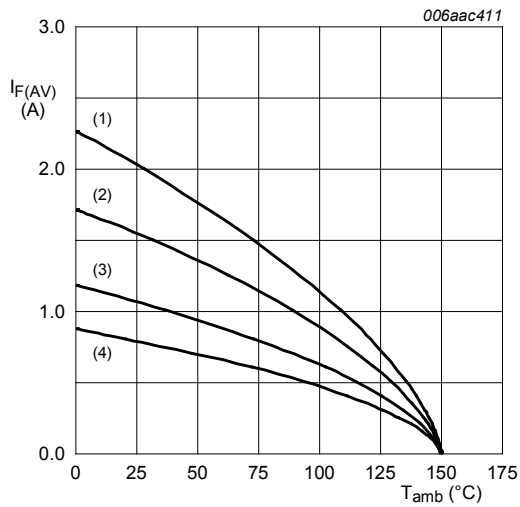
Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



$T_j = 85\text{ }^{\circ}\text{C}$

- (1) $\delta = 1$
- (2) $\delta = 0.9$
- (3) $\delta = 0.8$
- (4) $\delta = 0.5$

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

$T_j = 150\text{ °C}$

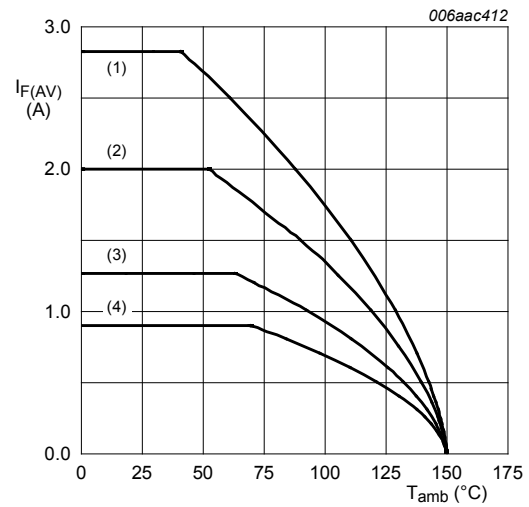
(1) $\delta = 1$; DC

(2) $\delta = 0.5$; $f = 20\text{ kHz}$

(3) $\delta = 0.2$; $f = 20\text{ kHz}$

(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm^2

$T_j = 150\text{ °C}$

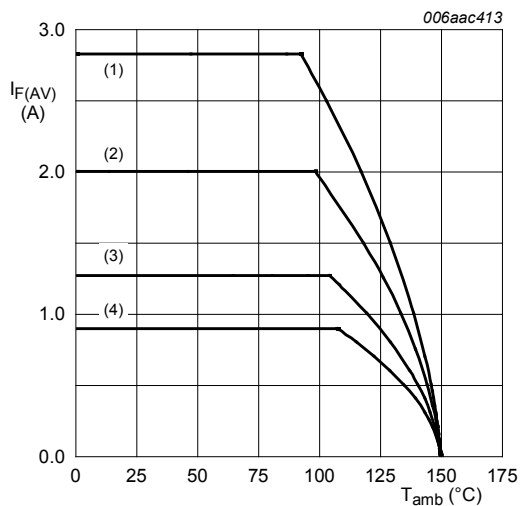
(1) $\delta = 1$; DC

(2) $\delta = 0.5$; $f = 20\text{ kHz}$

(3) $\delta = 0.2$; $f = 20\text{ kHz}$

(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al_2O_3 , standard footprint

$T_j = 150\text{ °C}$

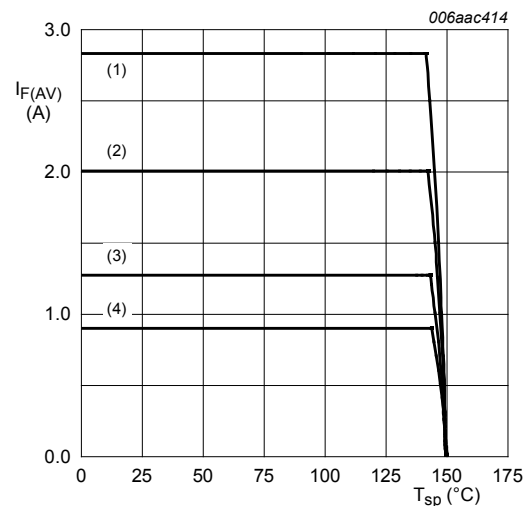
(1) $\delta = 1$; DC

(2) $\delta = 0.5$; $f = 20\text{ kHz}$

(3) $\delta = 0.2$; $f = 20\text{ kHz}$

(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 12. Average forward current as a function of ambient temperature; typical values



$T_j = 150\text{ °C}$

(1) $\delta = 1$; DC

(2) $\delta = 0.5$; $f = 20\text{ kHz}$

(3) $\delta = 0.2$; $f = 20\text{ kHz}$

(4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 13. Average forward current as a function of solder point temperature; typical values

11. Test information

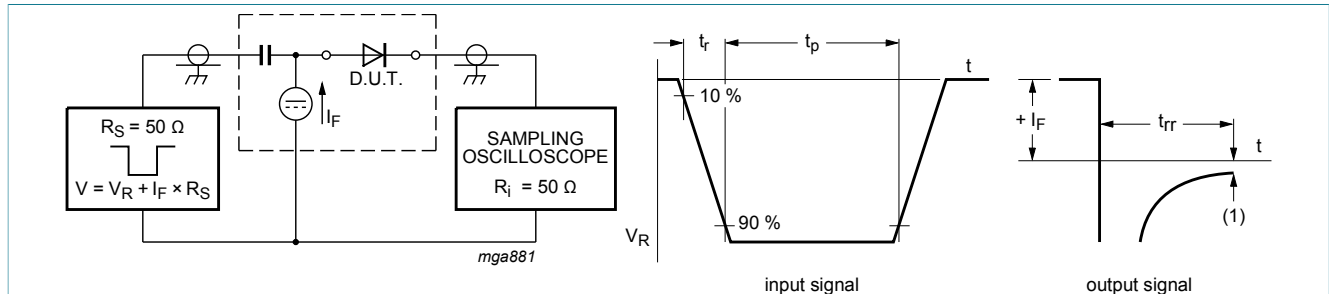


Fig. 14. Reverse recovery time: test circuit and waveforms

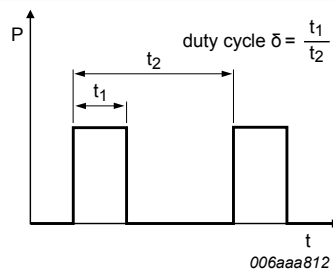


Fig. 15. Duty cycle definition

The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

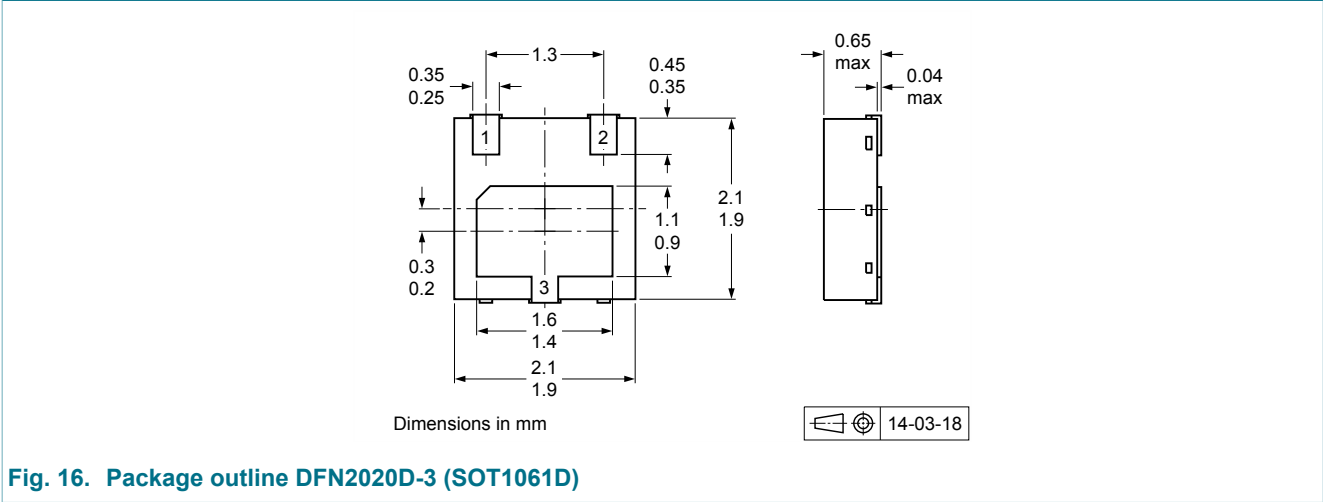


Fig. 16. Package outline DFN2020D-3 (SOT1061D)

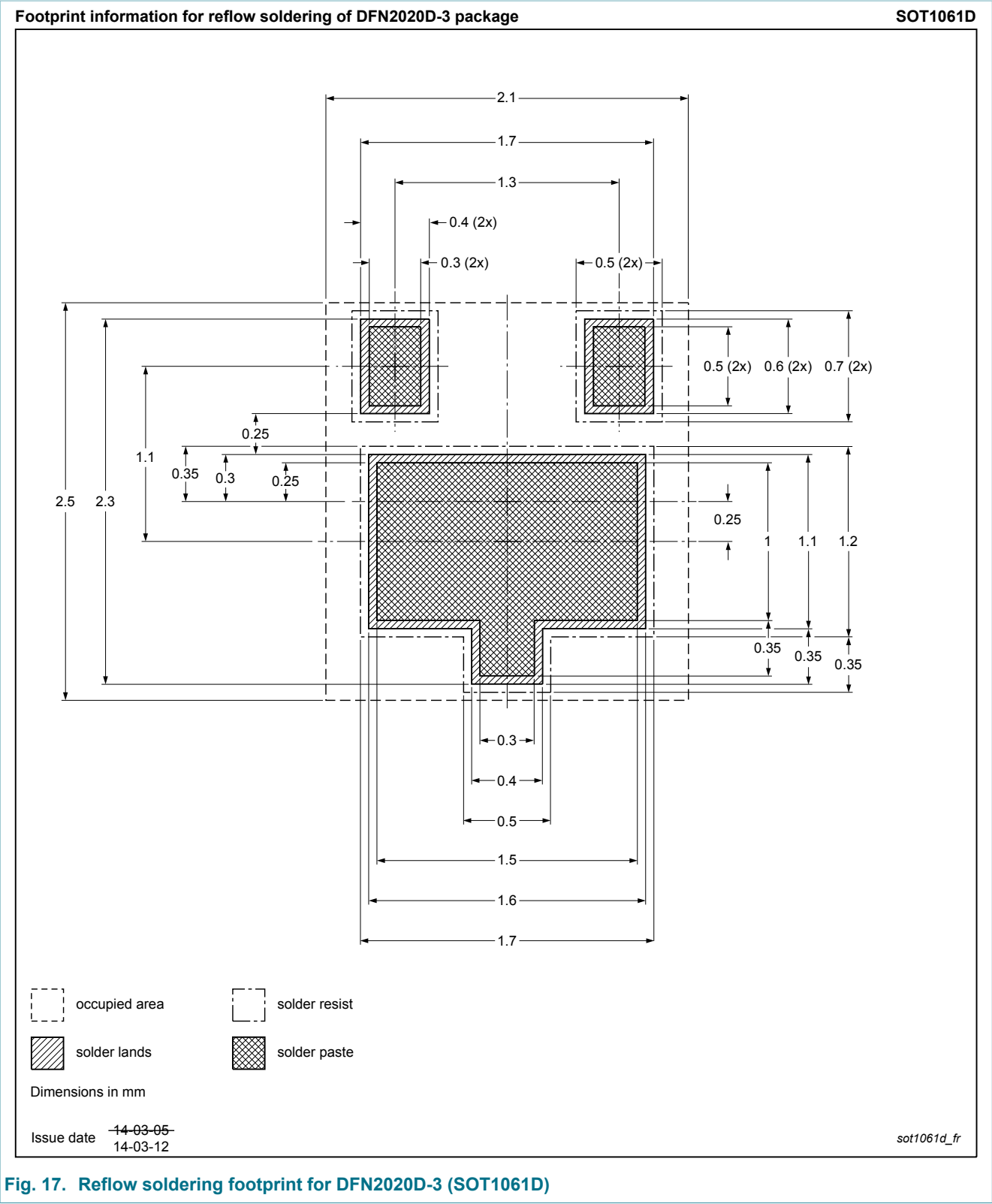


Fig. 17. Reflow soldering footprint for DFN2020D-3 (SOT1061D)

13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2020CPAS v.2	20150120	Product data sheet	-	PMEG2020CPAS v.1
Modifications:	changed data sheet status			
PMEG2020CPAS v.1	20141210	Preliminary data sheet	-	-

14. Legal information

14.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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